



SCHOTTKY DIODE MODULE TYPE 800A

Features

High Surge Capability
 Type 200V V_{RRM}
 Isolation Type Package
 Electrically Isolation base plate

HEAVY THREE TOWER**Maximum Ratings**

Operating Temperature : -55 °C to +150 °C

Storage Temperature : -55 °C to +150 °C

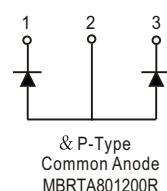
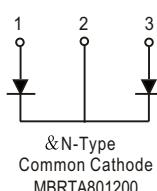
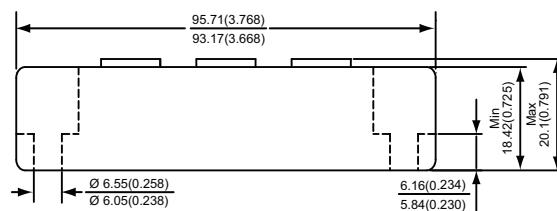
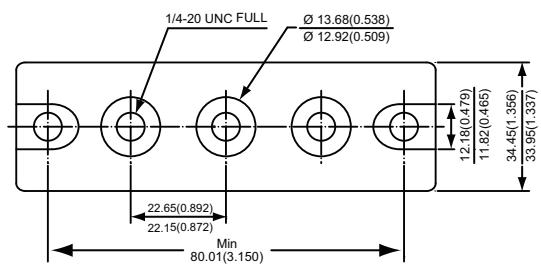
Dimensions in mm (1 mm = 0.0394")

Part Number	Maximum Recurrent Peak Reverse Voltage	Maximum RMS Voltage	Maximum DC Blocking Voltage
MBRTA801200(R)	200V	140V	200V

Electrical Characteristics @ 25 °C Unless Otherwise Specified

Average Forward Current (Per pkg)	I _{F(AV)}	800A	T _C = 100 °C
Peak Forward Surge Current (Per leg)	I _{FSM}	6200A	8.3ms , half sine
Maximum Instantaneous Forward Voltage (Per leg)	V _F	0.91 V	I _{FM} = 400A; T _J = 25 °C
Maximum Instantaneous Reverse Current At Rated DC Blocking Voltage * (Per leg)	I _R	5mA 10mA 80mA	T _J = 25 °C T _J = 100 °C T _J = 150 °C
Isolation Voltage	V _{ISOL}	3000 V	A.C. 1 minute
Maximum Thermal Resistance Junction To Case (Per leg)	R _{θJC}	0.25 °C/W	

*Pulse Test: Pulse Width 300 μsec, Duty Cycle 2%



MBRTA801200(R)



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Figure.1-Typical Forward Characteristics

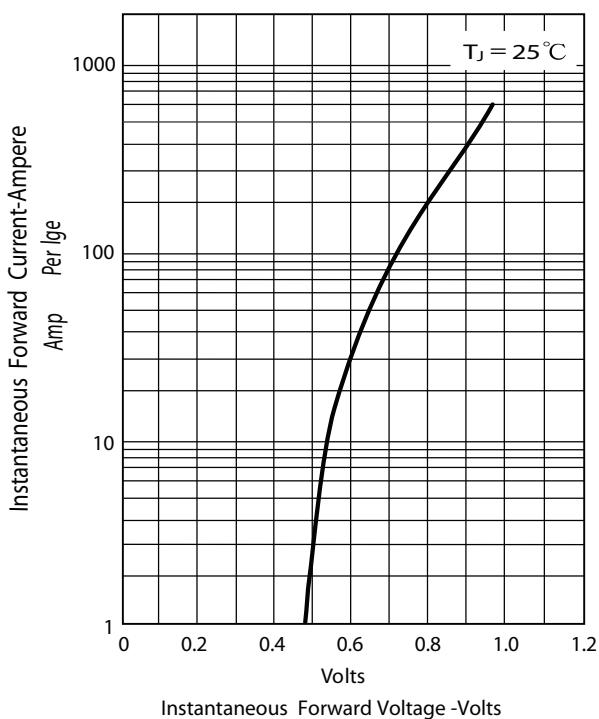
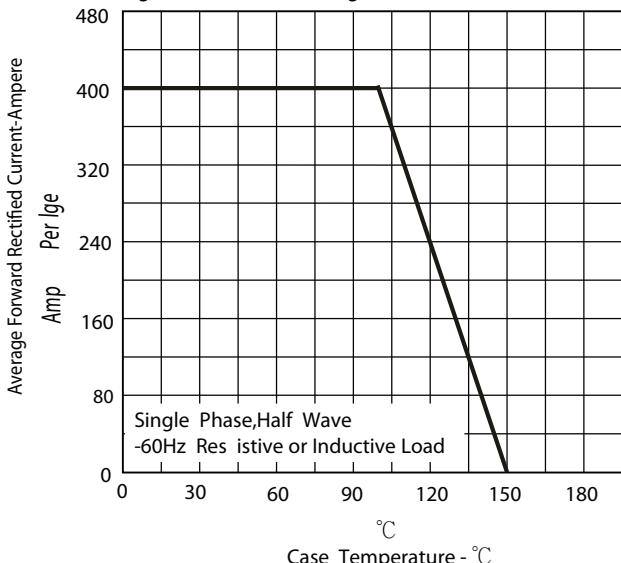


Figure.2-Forward Derating Curve



Instantaneous Forward Voltage -Volts

Figurpe.3-Peak Forward Surge Current

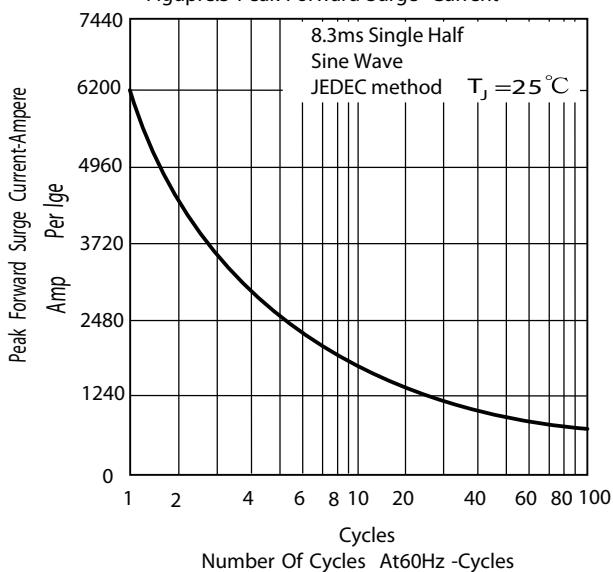


Figure.4-Typical Reverse Characteristics

